

Type Designator: 2SD64

Material of Transistor: Ge

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 0.12 W

Maximum Collector-Base Voltage [V_{cb}]: 25 V

Maximum Collector-Emitter Voltage [V_{ce}]: 20 V

Maximum Emitter-Base Voltage [V_{eb}]: 10 V

Maximum Collector Current [$I_{c \text{ max}}$]: 0.1 A

Max. Operating Junction Temperature (T_j): 150 °C

Transition Frequency (f_t): 0.5 MHz

Forward Current Transfer Ratio (h_{FE}), MIN: 40

Noise Figure, dB: -

Package: **TO18**